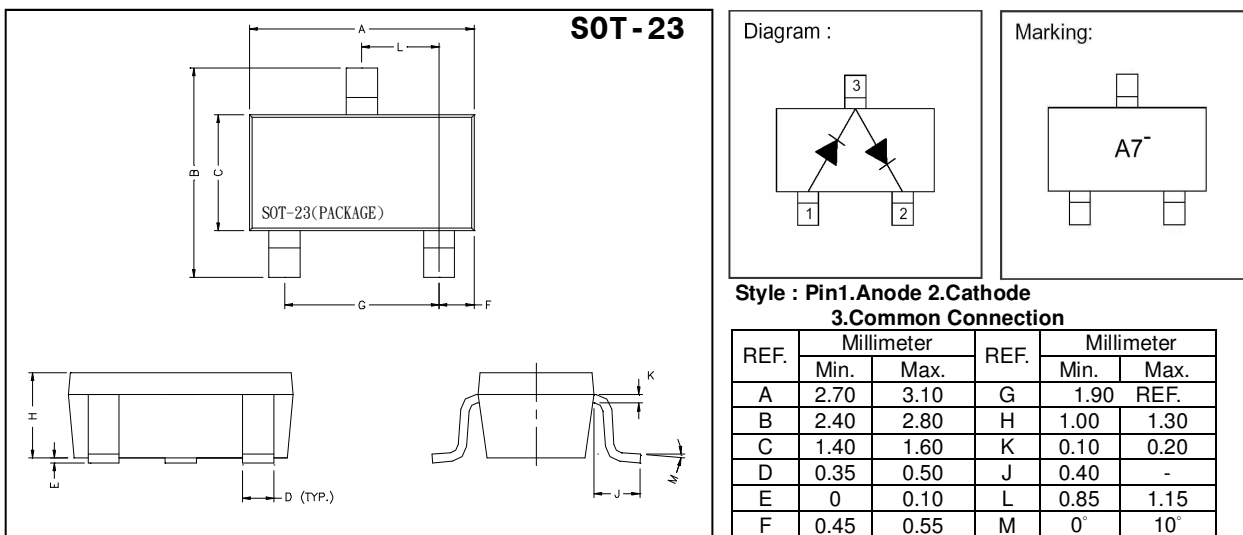


## GBAV99

### Description

The GBAV99 consists of two diodes in a plastic surface mount package. The diodes are connected in series and the unit is designed for high-speed switching application in hybrid thick and thin-film circuits.

### Package Dimensions



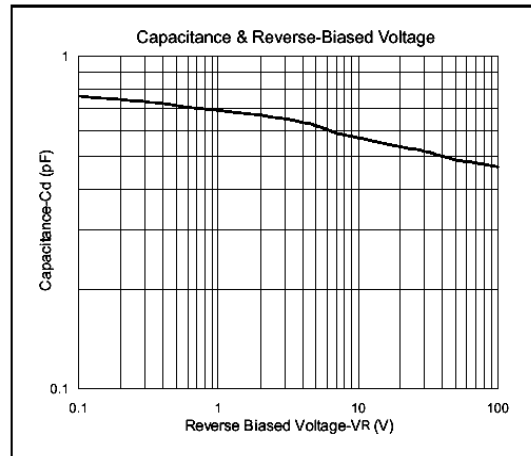
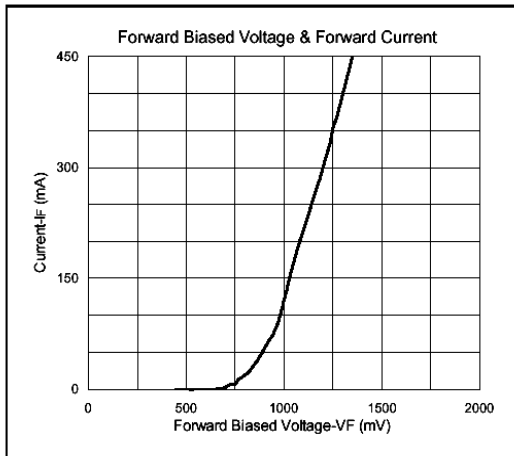
### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-65~+150	°C
Reverse Voltage		70	V
Repetitive Reverse Voltage		70	V
Forward Current		150	mA
Repetitive Forward Current		500	mA
Forward Surge Current(1ms)		1000	mA
Total Power Dissipation	PD	250	mW

### Characteristics at Ta = 25°C

Characteristic	Symbol	Min.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	V(BR)	70	-	V	IR=100uA
Forward Voltage	VF(1)	-	715	mV	IF=1mA
	VF(2)	-	855	mV	IF=10mA
	VF(3)	-	1000	mV	IF=50mA
	VF(4)	-	1250	mV	IF=150mA
Reverse Current	IR	-	2.5	uA	VR=70V
Total Capacitance	CT		1.5	pF	VR=0, f=1MHz
Reverse Recovery Time	Trr	-	6	nS	IF=IR=10mA, RL=100Ω measured at IR=1mA

## Characteristics Curve



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